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# Polymorphism in pentacene

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Pentacene,  $C_{22}H_{14}$ , crystallizes in different morphologies characterized by their d(001)-spacings of 14.1, 14.5, 15.0 and 15.4 Å. We have studied the crystal structure of the 14.1 and 14.5 Å *d*-spacing morphologies grown by vapour transport and from solution. We find a close correspondence between the 14.1 Å structure reported by Holmes, Kumaraswamy, Matzeger & Vollhardt [*Chem. Eur. J.* (1999), **5**, 3399–3412] and the 14.5 Å structure reported by Campbell, Monteath Robertson & Trotter [*Acta Cryst.* (1961), **14**, 705–711]. Single crystals commonly adopt the 14.1 Å *d*-spacing morphology with an inversion centre on both molecules in the unit cell. Thin films grown on SiO<sub>2</sub> substrates above 350 K preferentially adopt the 14.5 Å *d*-spacing morphology, with a slightly smaller unit-cell volume.

# Comment

Recently, molecular organic conductors were shown to exhibit a number of physical phenomena that were previously reserved for inorganic materials. This new development was triggered by the growth of ultrapure single crystals. In these crystals, the electronic mobility is comparable with singlecrystal silicon (Schön *et al.*, 2000*a*), which has been shown to be essential for phenomena such as electric-field-induced superconductivity (Schön *et al.*, 2000*b*), Quantum Hall oscillations (Schön, Berg *et al.*, 2000) and amplified spontaneous emission resulting in an injection laser (Schön, Kloc *et al.*, 2000). A number of molecular conductors were shown to exhibit these properties, such as  $C_{60}$ , thiophenes and the acenes. The acenes, from anthracene to hexacene, have been widely studied for electronic transport properties in the thin film as well as the single-crystal form.



The crystal structure of pentacene, (I), was reported by Campbell *et al.* (1961) for crystals grown from solution. They

constructed a triclinic crystal structure using 0kl and h0lWeissenberg films. The molecules are detected along the c axis with a d(001)-spacing of 14.5 Å. Because this d-spacing is by far the largest in this structure, it becomes characteristic for the structure. A much smaller *d*-spacing of 14.1 Å was recently reported by Holmes et al. (1999), also for crystals grown from solution. For thin films, different values for the d(001)-spacing have been reported, although the unit cell is not known. For thin films evaporated on  $SiO_2$  at temperatures above 350 K, a d-spacing of 14.5 Å has been reported (Minakata et al., 1992; Bouchoms et al., 1999). Lower substrate temperatures and different types of substrate result in thin films with *d*-spacings of 15.0 and 15.4 Å. We have studied the structure of single crystals, grown both from vapour transport and solution, in detail and report on the relationship between the 14.1 and 14.5 Å modifications.

We have grown single crystals of pentacene both by vapour transport and from a solution in trichlorobenzene. We found that both growth methods yield crystals with a *d*-spacing of 14.1 Å, in good agreement with Holmes et al. (1999). Despite the different *d*-spacings, the molecular ordering of the structures exhibit remarkable resemblances (Figs. 1 and 2). In order to compare the 14.1 Å morphology with the structure reported by Campbell et al. (1961), we transformed the 14.1 Å unit cell to yield a c axis that has approximately the length of the molecule of 16 Å. The three possible unit-cell transformations  $(100, 010, 1\overline{11}), (100, 010, 101)$  and  $(100, 010, \overline{111})$  result in caxis values of 16.01, 16.05 and 16.11 Å, respectively. Only for the last transformation does the long axis of the molecule runs approximately along the new c axis, which was also the guideline used by Campbell. This comparison shows that the 14.1 Å structure is very similar to the structure reported by Campbell et al. (1961) if we assume that their structure should be read in a left-handed coordinate system. We recall that the



### Figure 1

Stacking of the pentacene molecules in the unit cell, viewed along the  $[1\overline{10}]$  axis. The heart-lines of the pentacene molecules lie at angles of 25.17 (2) and 24.39 (2)°, respectively, with respect to the  $c^*$  axis. The d(001)-spacing is clearly visible.

determination of the handedness in triclinic systems was a very delicate problem at that time. Even with this identification, there remain discrepancies between the two solutions of almost 10° in the unit-cell angles, which is beyond standard deviations. These discrepancies concern the angles  $\alpha$  and  $\beta$ , the two angles that are important in determining the d(001)spacing and the discrepancies may have been the reason for a redetermination by Campbell et al. (1962), where the lattice parameters were revised, but not the angles.

We recall that the *d*-spacing of 14.5 Å reported by Campbell et al. (1961) is in fact observed in thin films. We deposited pentacene thin films on thermally oxidized Si wafers. The pentacene layer of  $2 \mu m$  thickness was then mechanically removed from the substrate and made into a powder. The diffraction pattern was measured in Bragg-Brentano and Guinier geometry and showed preferential orientation along the [001] axis. Besides the 14.5 Å phase, (00*l*) lines of the 14.1 and 15.4 Å phases were clearly observable. The 15.4 Å phase was transformed into the 14.5 Å phase by exposure to ethanol (Gundlach et al., 1999). The diffraction pattern could be indexed with a = 6.485 (1), b = 7.407 (2), c = 14.745 (4) Å,  $\alpha =$ 77.25 (2),  $\beta = 85.72$  (2),  $\gamma = 80.92$  (2)° and  $V = 681.6 \text{ Å}^3$ , yielding d(001) = 14.37 Å. This is in good agreement with



#### Figure 2

Perspective ORTEP-3 (Farrugia, 1997) drawing of the pentacene molecules at (a) 293 K and (b) 90 K, showing the non-H atom-numbering scheme. All C atoms are represented by displacement ellipsoids at the 50% probability level and the H atoms are drawn with arbitrary radii. Both molecules have a crystallographically imposed centre of inversion:  $C1-C11^{i}$  at  $(\frac{1}{2},\frac{1}{2},0)$  and  $C12-C22^{ii}$  at (0,0,0) [symmetry codes: (i) 1-x, 1 - y, -z; (ii) -x, -y, -z].

reports on the 14.5 Å *d*-spacing, but the unit-cell parameters are distinctly different from the values reported by Campbell et al. (1961, 1962). We will report this unit-cell determination separately. We conclude that pentacene exhibits at least four morphologies, which can be identified by their d(00l)-spacings. Single crystals commonly adopt the smallest d(001)-spacing of 14.1 Å. Thin films grown above 350 K adopt preferentially the 14.5 Å d(001)-spacing with a slightly smaller unit-cell volume.

# **Experimental**

The source material, 99.9% pure pentacene, was purchased from Aldrich and not purified further. Single crystals of pentacene were grown using physical vapour transport in a horizontal glass tube (Laudise et al., 1998). A temperature gradient was applied over the tube. The source material was sublimed at 550 K and crystallized at the other end of the tube at approximately 490 K. The growth was performed under a stream of N2 (99.999% purity, AGA gas) and H2 gases (99.995% purity, AGA gas), with a volume percentage of 5.1 (1)% H<sub>2</sub> [for (I) at 293 K]. This yielded almost centimetre-sized violet crystals in the form of platelets and needles. The  $c^*$  axis was normal to the plane of the very thin platelets (typically 10 to  $100 \,\mu m$ ) and the growth of the needles was along the  $[1\overline{10}]$  direction. Also, at a different part of the tube, a small amount of hydrogenated pentacene crystals (red needles) was found. Lowering the flow rate yielded a larger fraction of hydrogenated pentacene. At lower hydrogen content or if no ultrapure inert transport gas is used, the pentacene oxidizes, forming 6,13-pentacenequinone, and small brown needles crystallize (Dzyabchenko et al., 1979). The crystal structure of hydrogenated pentacene will be reported separately. Crystals were also grown from solution in trichlorobenzene by slowly evaporating the solvent over a period of four weeks at 450 K, under a stream of ultrapure N<sub>2</sub> gas. Crystals thus obtained [(I) at 90 K] exhibit the same crystal structure as the crystals grown by vapour transport. Pentacene thin films have been deposited using high-vacuum sublimation  $(10^{-8} \text{ mbar}; 1 \text{ mbar} = 100 \text{ Pa})$ . The source material was heated in a crucible and evaporated onto a thermally oxidized Si wafer heated to 370 K. A low evaporation rate of 0.1 nm s<sup>-1</sup> was used to ensure crystallinity and the sample was cooled rapidly afterwards. The layer thickness was 2 µm.

## Compound (I) at 293 K

(

Crystal data	
C <sub>22</sub> H <sub>14</sub>	Z = 2
$M_r = 278.35$	$D_x = 1.349 \text{ Mg m}^{-3}$
Triclinic, $P\overline{1}$	Mo $K\alpha$ radiation
a = 6.266 (1)  Å	Cell parameters from 23
b = 7.775 (1)  Å	reflections
c = 14.530(1)  Å	$\theta = 17.9 - 21.7^{\circ}$
$\alpha = 76.475 \ (4)^{\circ}$	$\mu = 0.08 \text{ mm}^{-1}$
$\beta = 87.682 \ (4)^{\circ}$	T = 293  K
$\gamma = 84.684 \ (4)^{\circ}$	Needle-block, violet
$V = 685.15 (15) \text{ Å}^3$	$0.10 \times 0.08 \times 0.08 \ \mathrm{mm}$
Data collection	
Enraf–Nonius CAD-4F diffrac-	$\theta_{max} = 26.0^{\circ}$

Enraf-Nonius CAD-4F diffractometer  $\omega/2\theta$  scans 2856 measured reflections  $l = -17 \rightarrow 17$ 2684 independent reflections 3 standard reflections 843 reflections with  $I > 2\sigma(I)$  $R_{\rm int} = 0.034$ 

 $-7 \rightarrow 6$ 

frequency: 180 min

 $= -6 \rightarrow 9$ 

#### Refinement

Refinement on  $F^2$ R(F) = 0.069 $wR(F^2) = 0.179$ S = 0.942684 reflections 199 parameters

### Compound (I) at 90 K

Crystal data

 $C_{22}H_{14}$  $M_r = 278.35$ Triclinic, P1 a = 6.239(1) Å b = 7.636(1) Å c = 14.330(2) Å  $\alpha = 76.978(3)^{\circ}$  $\beta = 88.136(3)^{\circ}$  $\gamma = 84.415(3)^{\circ}$  $V = 661.94 (17) \text{ Å}^3$ 

#### Data collection

Bruker SMART APEX diffractometer  $\varphi$  and  $\omega$  scans Absorption correction: multi-scan (SADABS; Bruker, 2000)  $T_{\min} = 0.981, T_{\max} = 0.999$ 5619 measured reflections

#### Refinement

Refinement on $F^2$	All H-atom parameters refined
R(F) = 0.045	$w = 1/[\sigma^2(F_o^2) + (0.0643P)^2]$
$wR(F^2) = 0.145$	where $P = (F_o^2 + 2F_c^2)/3$
S = 0.97	$(\Delta/\sigma)_{\rm max} < 0.001$
2584 reflections	$\Delta \rho_{\rm max} = 0.26 \ {\rm e} \ {\rm \AA}^{-3}$
255 parameters	$\Delta \rho_{\rm min} = -0.20 \text{ e } \text{\AA}^{-3}$

The needle axis appeared to be along the  $[1\overline{10}]$  vector (9.52 Å) in the chosen (standard) unit-cell setting. The studied plate-shaped crystals were all twinned and the plane normal is along the  $c^*$  axis (meaning the *a* and *b* axes in the plate). The relation between the twin orientations is a  $180^{\circ}$  rotation around the  $[1\overline{1}0]$  axis (rotation matrix:  $0\overline{1}0$ ,  $\overline{100}$ ,  $00\overline{1}$ ). Although an X-ray structure determination was thwarted by persistent crystal twinning and the weak scattering power of the crystals, we ultimately found a single crystal (needle-shaped) fit to the X-ray diffraction experiment.

For compound (I) at 293 K, data collection: CAD-4-UNIX Software (Enraf-Nonius, 1994); cell refinement: SET4 (de Boer & Duisenberg, 1984); data reduction: HELENA (Spek, 1997); program(s) used to solve structure: SHELXS97 (Sheldrick, 1997); program(s) used to refine structure: SHELXL97 (Sheldrick, 1997);

H-atom parameters constrained  $w = 1/[\sigma^2(F_o^2) + (0.0608P)^2]$ where  $P = (F_o^2 + 2F_c^2)/3$  $(\Delta/\sigma)_{\rm max} < 0.001$  $\Delta \rho_{\rm max} = 0.14 \ {\rm e} \ {\rm \AA}^{-3}$  $\Delta \rho_{\rm min} = -0.21 \text{ e} \text{ Å}^{-3}$ 

Z = 2 $D_{\rm r} = 1.396 {\rm Mg} {\rm m}^{-3}$ Mo  $K\alpha$  radiation Cell parameters from 1062 reflections  $\theta = 2.8 - 26.1^{\circ}$  $\mu = 0.08 \text{ mm}^{-1}$ T = 90 KPlatelet, violet-blue  $0.25 \times 0.24 \times 0.01 \text{ mm}$ 

2584 independent reflections 1252 reflections with  $I > 2\sigma(I)$  $R_{\rm int} = 0.030$  $\theta_{\rm max} = 26.1^\circ$  $h = -7 \rightarrow 7$  $k = -9 \rightarrow 9$  $l = -15 \rightarrow 17$ 

molecular graphics: PLUTO (Meetsma, 2000) and PLATON (Spek, 1994); software used to prepare material for publication: PLATON (Spek, 1990).

For compound (I) at 90 K, data collection: SMART (Bruker, 2000); cell refinement: SAINT (Bruker, 2000); data reduction: XPREP (Bruker, 2000); program(s) used to solve structure: SIR97 (Altomare et al., 1997); program(s) used to refine structure: SHELXL97 (Sheldrick, 1997); molecular graphics: PLUTO (Meetsma, 2000), ORTEP-3 (Farrugia, 1997; Johnson et al., 2000) and PLATON (Spek, 1994); software used to prepare material for publication: PLATON (Spek, 1990) and SHELXL97.

Supplementary data for this paper are available from the IUCr electronic archives (Reference: SK1477). Services for accessing these data are described at the back of the journal.

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